

Attorney Docket No.: P12659

**AMENDMENTS TO THE CLAIMS**

Please amend the claims as follows:

13. (Currently amended) A microelectronic die package comprising:

a microelectronic die including:

a die substrate;

a layer of dielectric mounted to the die substrate; and

a thermally conductive material ~~disposed in an inner region~~ located between the die substrate and the layer of dielectric and defining thermal contact zones; and

~~thermal contact elements disposed between an outer region located outside of the inner region and~~ a heat dissipation device in thermal contact with the thermally conductive material disposed in the inner region thermal contact zones to effect a dissipation of heat away from the die.

14. (Cancelled)

15. (Currently amended) The microelectronic die package according to claim 13, wherein: ~~the thermally conductive material comprises a layer of thermally conductive material;~~ the die substrate defines at least one via a plurality of vias therein, at least some of the layer of thermally conductive material being located in the vias at least one via, ~~the at least some of the layer of thermally conductive material further defining to~~

**Attorney Docket No.: P12659**

define the thermal contact zones ~~and being in thermal contact with the thermal contact elements.~~

16-17 (Cancelled)

18. (Original) The microelectronic die package according to claim 13, further comprising an adhesion promoter disposed between the thermally conductive material and the die substrate to enhance an adhesion of the layer of thermally conductive material to the die substrate.

19-21 (Cancelled)

22. (Currently amended) ~~A thermally conductive microelectronic die substrate for a microelectronic die comprising:~~

a die substrate; and

a layer of dielectric mounted to the die substrate; and

a thermally conductive material located between the die substrate and the layer of dielectric ~~provided on the die substrate~~ and defining thermal contact zones adapted to be connected to a heat dissipation device ~~configured to effect a~~ dissipation of heat away from the die.

23. (Cancelled).

**Attorney Docket No.: P12659**

24. (Currently amended) The thermally conductive microelectronic die substrate according to claim 23, wherein:

the die substrate comprises a silicon wafer;

~~the layer of dielectric comprises a layer of silicon mounted to the silicon wafer;~~

and

the thermally conductive material comprises a layer of copper in the inner region, the silicon wafer further defining a plurality of vias ~~at least one via~~ therein, and some of the layer of copper being disposed in the plurality of ~~at least one vias~~ to define the thermal contact zones.

25. (Currently amended) A microelectronic die package comprising:

a microelectronic die comprising:

a die substrate;

a layer of dielectric mounted to the die substrate;

~~means disposed in an inner region located between the die~~  
substrate and the layer of dielectric for effecting a dissipation of heat away from the die microelectronic circuit; and

means in thermal contact with the means for effecting for directing heat away from the die through the means for effecting.

26. (Original) The die according to claim 25, wherein the means for effecting comprises a layer of copper.

**Attorney Docket No.: P12659**

27. (Original) The die according to claim 25, wherein the means for directing comprises a heat dissipation device.